Design, Assembly and Commissioning of a Test Apparatus for Characterizing Thermal Interface Materials

J.R. Culham, P. Teertstra, I. Savija and M.M. Yovanovich

Microelectronics Heat Transfer Laboratory
University of Waterloo
Waterloo, Canada N2L 3G1

ITherm 2002
San Diego, CA May 29 - June 1

Outline

- Motivation
- Background
- Test Procedure
- Design Alternatives
- Test Apparatus
- Summary

Objectives

- measure resistance and thermal conductivity
  - ✓ grease, compliant polymers, metal foils, graphite, phase change, etc.
  - ✓ interface pressure: 5 - 1000 psi
  - ✓ interface temperature: 0 - 120 ^{o}C
  - ✓ in-situ thickness and resistance versus load

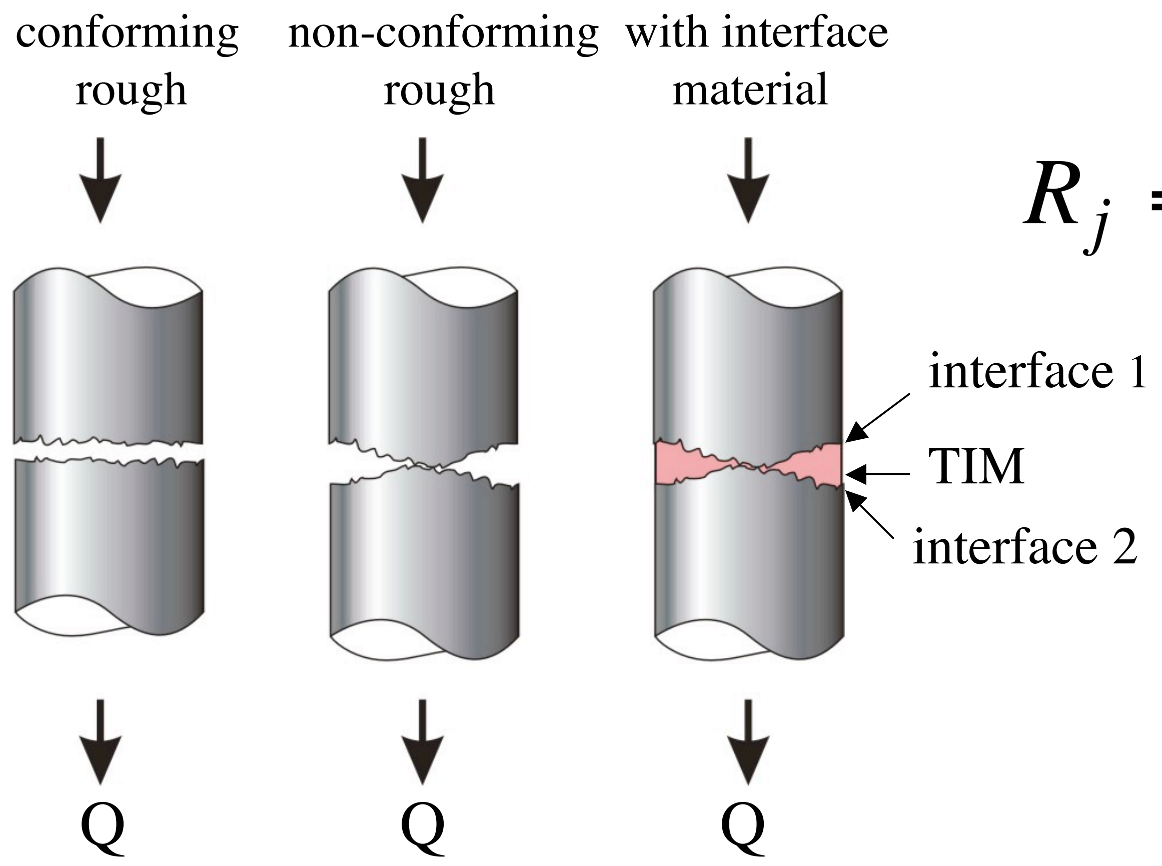
Microelectronics Heat
Transfer Laboratory
University of Waterloo

Motivation

- ASTM D 5470
  - ✓"thin thermally conductive solid electrical insulation materials"
    - thickness range of 0.02 to 10 mm
    - apparent thermal conductivity based on "as-received" thickness
    - interface pressure - 3.0 MPa
    - interface temperature - 50 ^{o}C
    - surface roughness less than 0.4 μm

Microelectronics Heat
Transfer Laboratory
University of Waterloo

Thermal Interface



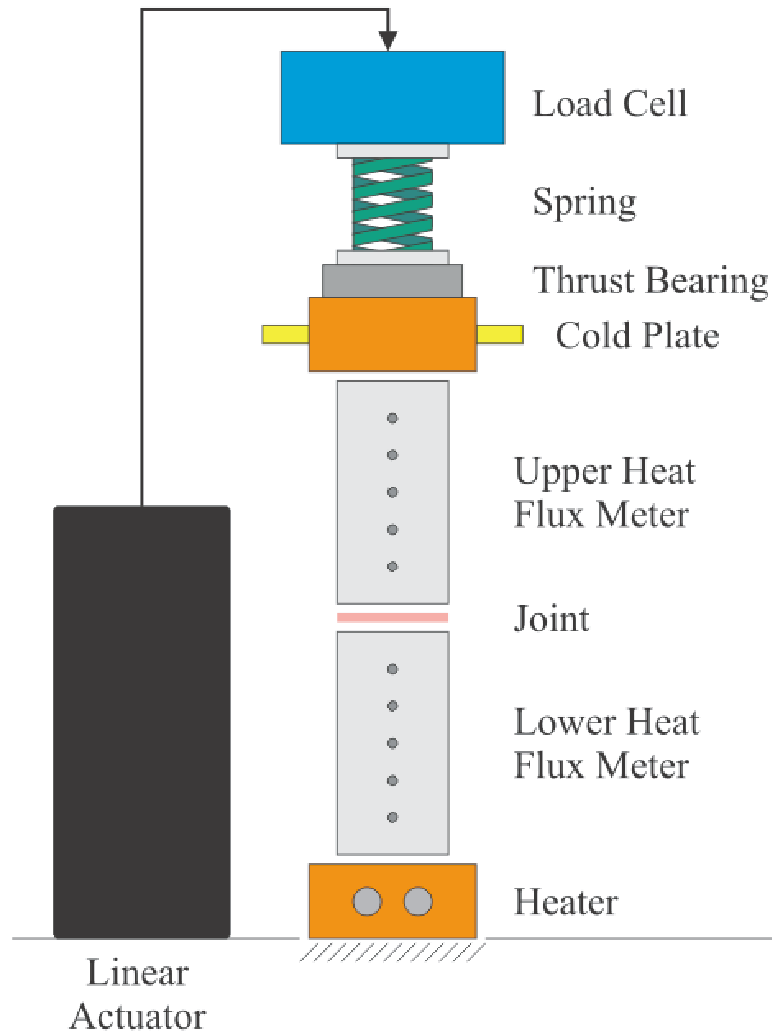
$$R_j = R_{i1} + R_{TIM} + R_{i2}$$

where:

$$R_{TIM} = \left(\frac{t}{k\,A} \right)_{TIM}$$

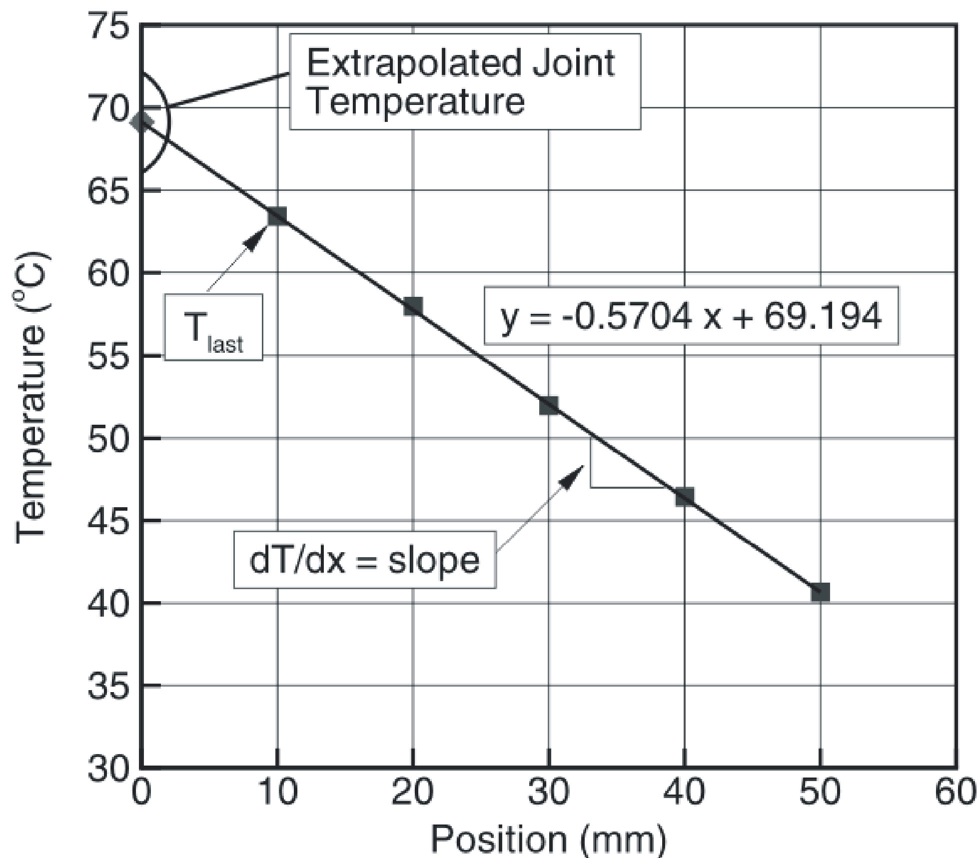
Microelectronics Heat
Transfer Laboratory
University of Waterloo

Test Procedure



- for an applied axial load
  - ✓ establish desired interface temperature with resistance heaters
  - ✓ minimize heat losses using a vacuum environment
  - ✓ establish steady-state in 5 upper & lower temperature sensors
  - ✓ record & reduce temperature data to determine interface temperature rise and heat flow rate

Data Analysis



- Using a linear least squares fit
  - ✓ curve fit temperature data for upper & lower heat flux meter
  - ✓ slope gives temperature gradient
  - ✓ extrapolate to get interface temperatures
  - ✓ knowing the thermal conductivity of the flux meters, calculate heat flow rate
  - ✓ then, $R_i = \Delta T_i / Q$

Temperature Measurement Alternatives

	Thermocouple	Platinum RTD	Semiconductor	Thermistor
Sensor	thermo electric	film resistor	semiconductor	ceramic
Accuracy	0.5 ºC	0.1 ºC	0.5 ºC	0.05 ºC
Stability	prone to aging	0.05 ºC/year	1.0 ºC/year	0.02-0.2 ºC/year
Linearity	non-linear	linear	linear	exponential
Response Time	0.1 – 10 sec.	1 – 50 sec.	5 – 50 sec.	0.5 – 10 sec.
Cost	low	high	moderate	moderate

Thermal Conductivity Measurement

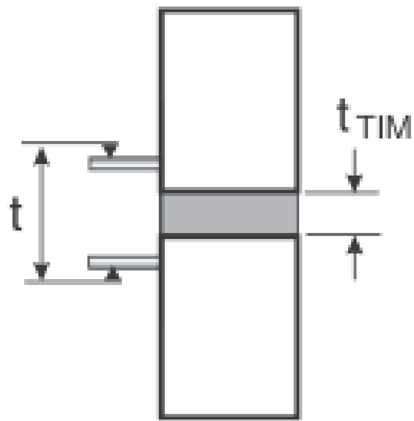
- interface material thermal conductivity:

$$k_{TIM} = \frac{Q}{\Delta T_{TIM}} \frac{t_{TIM}}{A_{TIM}}$$

- ASTM D 5470 recommends using the "as-received" thickness
- material deformation during testing
  - ✓ loading
  - ✓ thermal expansion
- in-situ thickness measurement is required

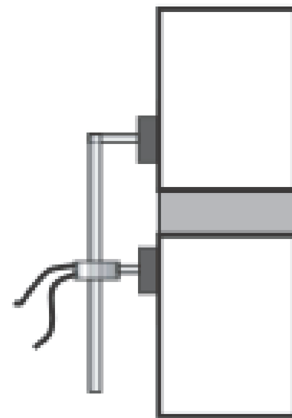
In-situ Thickness Measurement Alternatives

$t_{TIM} = t - t_{start}$



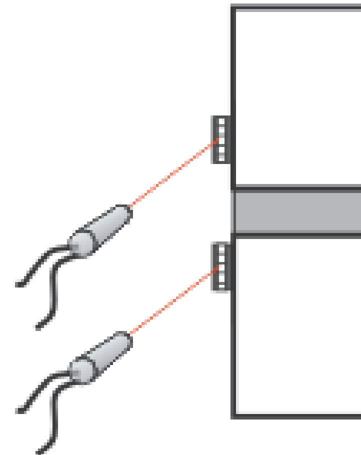
a) direct measurement

- dial gauge or micrometer
- measurement resolution: 100 μm
- cannot be used in vacuum



b) LVDT

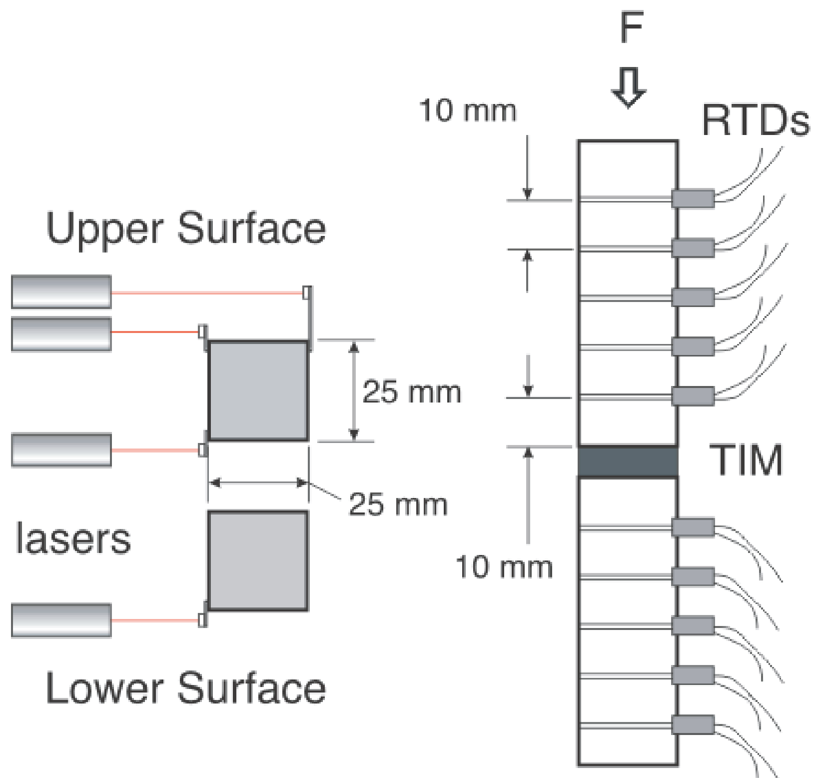
- linear variable differential transformer
- measurement resolution: 0.5 μm
- physical limitations



c) laser / detector

- 5 mW laser
- 6x1 mm detector (1 gram)
- Measurement resolution: 0.75 μm

In-situ Thickness Measurement Alternatives



- 2 laser system
  - ✓ relative displacement
- 4 laser system
  - ✓ relative displacement
  - ✓ out-of-flatness

Microelectronics Heat
Transfer Laboratory
University of Waterloo

Test Apparatus

- load range: up to 1000 psi (7 MPa)
- interface temperature: -10 ^{o}C to 150 ^{o}C
- vacuum pressure: 10^{-4} torr
- data collection rate: 0.1 seconds

Microelectronics Heat
Transfer Laboratory
University of Waterloo

ITherm 2002

San Diego, CA May 29 - June 1

Microelectronics Heat
Transfer Laboratory
University of Waterloo

CONCORDIA CUM VERITATE

ITherm 2002

San Diego, CA May 29 - June 1

Microelectronics Heat
Transfer Laboratory
University of Waterloo

ITherm 2002

San Diego, CA May 29 - June 1

Microelectronics Heat
Transfer Laboratory
University of Waterloo

Cost

- Test Column - $3,700
- Vacuum System - $5,400
- Data Acquisition - $3,800
- In-situ Thickness Measurement - $3,800
- Miscellaneous - $7,100
- Total - $23,800

Summary

- Thermal interface test apparatus designed and built:
  - ✓ in-situ thickness measurement with sub-micron precision
  - ✓ overall energy balance to within ±2%
  - ✓ thermal resistance and thermal conductivity measurements to within ±3%

Microelectronics Heat
Transfer Laboratory
University of Waterloo

Acknowledgments

- We acknowledge the financial support of:
  - ✓Natural Sciences & Engineering Research Council of Canada
  - ✓Centre for Microelectronic Assembly & Packaging
  - ✓R-Theta Inc., Mississauga, ON
- We acknowledge the technical assistance of Mr. Dave McClafferty, IBM, Poughkeepsie

Microelectronics Heat Transfer Laboratory
University of Waterloo